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Raman spectra of gallium sulfide based glasses

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Abstract

Raman investigation of glasses $x \text{GeS}_2 - \text{Ga}_2 \text{S}_3 - y \text{MCl}$, $\text{Ga}_2 \text{S}_3 - 2 \text{MCl}$ (where M = Ag, Tl, Rb, Cs) and melt $\text{Ga}_2 \text{S}_3 - 2 \text{CsCl}$ has been carried out for various x and y. Raman spectra have been interpreted in the frame of the model that gallium is fourfold coordinated in the chalcogenide/halide glasses and forms complex anions such as $[\text{GaS}_{3/2}\text{Cl}]^{1-}$. Stability of these units and type of their interconnection (corner shared or edge shared tetrahedra) depends on cation radius of a metal and correlates with glass-forming ability.

1. Introduction

Germanate and gallate, Ga₂O₃-M_xO (M - metal), glasses are well known and studied. It was found by nuclear spin resonance (NMR) [1], X-ray absorption [2], infra-red (IR) and Raman spectroscopy [3], that Ge and Ga have tetrahedral environments. The glasses including sulfur instead of oxygen are less studied. The compound GeS₂ is a network glass former and its IR and Raman spectra can be well interpreted based on the vibrational modes of tetrahedral pseudomolecular subunits GeS_{4/2} (breathing mode 342 cm⁻¹) [4]. The pure compound Ga₂S₃ can be transformed into the glassy state only as film [5]. Recently bulk glasses containing gallium sulfide have been produced [18,9,15]. The structure of these glasses is still a topic of discussion.

The aim of this work is structural investigation of Ga₂S₃ based glasses by Raman spectroscopy.

2. Experiment

2.1. Sample preparation

The samples were synthesized from metal chloride, gallium and sulfur at a high temperature in a quartz ampoule which had been sealed under vacuum. AgCl was produced by dissolving silver in nitric acid and then precipitating it by HCl. The other metal chlorides, sulfur and gallium were commercial reagents (Reachem). All the chlorides had been dried thoroughly just before synthesis. The syntheses were carried out at temperatures 1000–1150°C for 4–10 h in the rocking furnace. The samples (in an ampoule) were vitrified by quenching in water or air. The choice of cooling rate depended on glass-forming ability. TlGaS_{1.5}Cl melt was quenched by splash

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cooling on a rotating copper wheel (cooling rate 10^4-10^5 K/s). The glassy state of all samples was confirmed by X-ray analysis.

2.2. Raman spectroscopy

The setup consists of Kr ion laser at 647.1 nm and a 1 m double monochromator (Jobin Yvon U1000, 1800 lines/mm) with photon counting (dark count rate 1/s). Spectra were taken using 512 channels, 1 cm⁻¹ each, at incident beam powers of 100–500 mW, on the Stokes side. Measurements were carried out at 90°, with samples placed into sealed cylindrical quartz ampoules.

3. Results

In order to investigate non-crystalline Ga_2S_3 structure, we synthesized glass with mixed $(GeS_2)_{(0.8)}(Ga_2S_3)_{(0.2)}$ composition. In Fig. 1 we present the reduced Raman spectra of $(GeS_2)_{(1-x)}(Ga_2S_3)_{(x)}$ glasses for x=0 (pure GeS_2) and x=0.2 (the procedure of the reduction was proposed by Galeener and Sen [19]). The spectra show that insertion of a relatively small quantity of Ga_2S_3 into GeS_2 glass former leads only to the redistribution of intensity in the 350-420 cm⁻¹ range and to displacement of the lower frequency peak from 258 cm⁻¹ to 268 cm⁻¹. A similar Raman curve shape was obtained for the samples with $x \sim 0.18$ and $x \sim 0.07$ [6]. The glasses which include

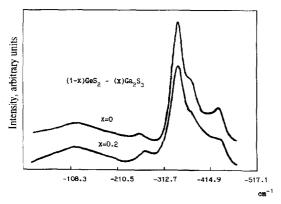


Fig. 1. Reduced Raman spectra of glasses $(1 - x)GeS_2 - (x)Ga_2S_3$, where x = 0, 0.2.

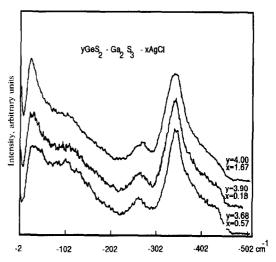


Fig. 2. Raman spectra of $yGeS_2-Ga_2S_3-xAgCl$ glasses.

metal ions are of a great significance for applications. However, the glass-forming regions of the mixed systems including metal salts have quite a narrow composition range. Taking into account the tendency of Ga towards fourfold coordination and formation of tetrahedral complexes (e.g., $[GaCl_4]^{1-}$), it was of interest for us to add metal halides to glasses containing Ga_2S_3 , e.g., to $GeS_2-Ga_2S_3$, and also to pure Ga_2S_3 in order to bind the metal ions with a fourfold network formed by tetrahedral coordinated Ga. Indeed we have found glass formation in broad composition regions of the gallium sulfide

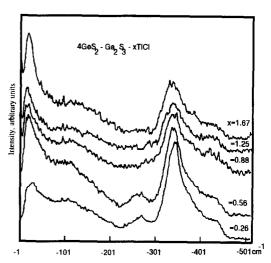


Fig. 3. Raman spectra of $4GeS_2 - Ga_2S_3 - xTlCl$ glasses.

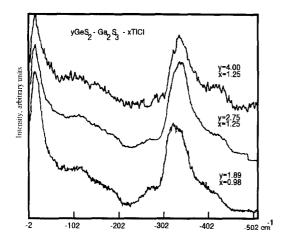


Fig. 4. Raman spectra of $yGeS_2-Ga_2S_3-xTICl$ glasses.

systems with various metal halides [9]. Here we will discuss AgCl, TlCl, RbCl and CsCl additions.

Phase diagrams show that metal chlorides don't interact with GeS_2 [10], therefore we assume that metal chloride additions interact with Ga_2S_3 only and we can extract the information about the interaction from Raman spectra.

We were able to produce glasses containing up to 39 mol% AgCl in the GeS₂-Ga₂S₃-AgCl system [9]. Raman spectra are depicted in Fig. 2. If AgCl content is increasing, at an essentially constant ratio of GeS₂ to Ga₂S₃, the shape of the Raman spectrum shows only negligible changes. This fact seems to

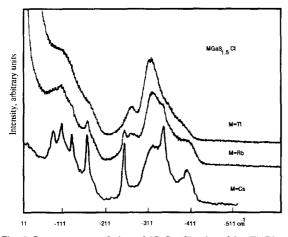


Fig. 5. Raman spectra of glassy $MGaS_{1.5}Cl$, where M = Tl, Rb or Cs.

Table 1 Ion radius calculated according to Goldschmidt (*1) and Pauling (*2)

Metal	Ion radius A		
	* 1	* 2	
Ag	1.13	1.26	
Tl	1.49	1.44	
Rb	1.49	1.48	
Cs	1.65	1.69	

prove that AgCl does not interact with the GeS₂-Ga₂S₃ glass matrix.

Studying the $GeS_2-Ga_2S_3-TICI$ system, we have found that the glass-forming composition region is broader (viz about a factor of two) than one in the AgCl system [9]. Also, there is some difference from the previous system in the Raman spectra (see Fig. 3). Increasing the TlCl contents at a constant ratio of GeS_2 to Ga_2S_3 (4:1) leads to two major effects. The

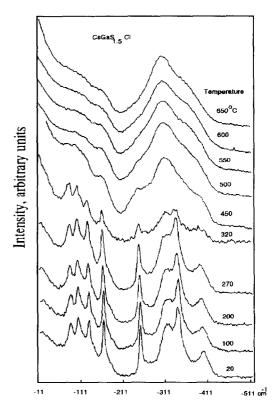


Fig. 6. Raman spectra of CsGaS_{1.5}Cl in the glassy and melt states at different temperatures (from 20 to 650°C).

first, the breathing mode line of GeS_2 glass (structure units $GeS_{4/2}$, 342 cm⁻¹) is broadened to the lower frequency side; later we shall show that this is due to the addition (and/or mixing) of the breathing mode contribution at ~320 cm⁻¹ of $GaS_{3/2}CI^{-1}$ structure subunits. The second, the peak disappears at 268 cm⁻¹. Besides, the increase of Ga_2S_3 content (at approximately constant TIC1 content) results in the shift of the band from 340 cm⁻¹ to 320 cm⁻¹ (see Fig. 4).

The glass-forming composition region of systems containing Ga_2S_3 –MCl only (M – metal), increases according to increasing of metal ion radius [9]. Raman spectra of glasses MGaS_{1.5}Cl, where M = Tl, Rb, Cs, are represented in Fig. 5. This is a sequence of ions with increasing radius of M⁺ (see Table 1). There is a pronounced difference between the spectra of the glasses containing Tl and Cs while the spectrum Rb including glass is close to a superposition of the two other spectra.

The heating of glassy CsGaS_{1.5}Cl up to melt state results in disappearing of this difference (Raman spectra of both glassy and melt CsGaS_{1.5}Cl are represented in Fig. 6).

4. Discussion

In the Raman spectrum of glassy Ge_xS_{1-x} (GeS_2 glass for example, see Fig. 1), the peak at 258 cm⁻¹ has been ascribed to the stretching of the direct Ge-Ge bond in the subunits of the

type (e.g., $Ge_2S_{6/2}$) [7]. In glassy stoichiometric composition these homobonds exist due to concentration fluctuations. Their content is relatively low and depends on glass preparing regime. Certainly this peak is pronounced in glassy Ge_xS_{1-x} at x > 0.33 (i.e., where there is a chalcogen deficit relative to stoichiometric GeS_2), at x = 0.37 for example [4]. The existence of Ge-Ge homobonds in Ge-S glasses was also confirmed by Feltz et al. with ESCA [8].

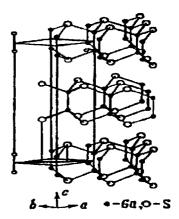


Fig. 7. GaS crystal structure.

We propose to assign the 268 cm⁻¹ line in Raman spectra of gallium sulfide containing glasses (see Fig. 1, x = 0.2) to a stretching of the Ga–Ga bond in a complex subunit

in an analogous way ¹. A slightly higher frequency (by 3.8%) would be in accordance with the somewhat smaller mass of Ga compared to Ge (by 4.2%), so that 2.1% frequency shift is expected (to 263 cm⁻¹). A small discrepancy may be due to the difference between the force constants. We have some additional reasons for such assumption. This complex unit

does not contradict GaS crystal structure (see Fig. 7). Besides, the peak intensity depends on the ratio of Ga and S components as in the Ge-S system. The increase of Ga contents relative to S results in the increase of the band intensity [6,15].

¹ At any rate, two sulfur atoms of this structure unit are threefold coordinated $(Ga_2S_{4/2}S_{2/3})$.

In the gallium sesquisulfide-germanium disulfide-metal chloride glass systems, when the ratio of Ga-X (X – chalcogen or galogen) components amounts to 1:4, i.e., the possibility of fourfold coordination of gallium by chalcogen/halogen takes place (GaX_4), the peak disappears at 268 cm⁻¹ (with the exception of the system with AgCl, Fig. 2). The disappearance of the above mentioned mode of the

bond with the increasing TlCl content (see in Fig. 3) can probably be explained by the formation of a complex anion: instead of

homobonds,

heterobonds appear. This statement is in agreement with the set of spectra shown in Fig. 4, where the ratio of GeS₂ to Ga₂S₃ is changed at approximately constant TlCl content. Here one can see an intensity shift from the band at 340 cm⁻¹ (ratio 4:1) to a position around 320 cm⁻¹ (ratio 1.88:1). Summarizing both observations we conclude that, when Cl-Ga bonds become possible due to addition of metal chloride to a Ga₂S₃ containing glass, fourfold coordination of Ga by sulfur and chlorine develops, and that the breathing mode of such tetrahedra is about 320 cm⁻¹. The idea of mixed halogen-chalcogen environment of Ga in the glassy state was also considered [11,17].

Formation of such tetrahedra assists glass formation, therefore there is a possibility of glass formation even without a GeS₂ glass-forming matrix. In-

deed we have found wide glass-forming regions in the Ga_2S_3 -MCl systems [9].

According to the previously mentioned facts, we argue that the effects of the interaction of Ga_2S_3 with TlCl are similar both with and without the GeS_2 component. It is obvious, for example, of $TlGaS_{1.5}Cl$ glass. The Raman spectrum shown in Fig. 5(a) can be explained satisfactorily within the framework of the above described model as a superposition of the contributions from pseudomolecular subunits

Both our Raman data of glassy TlGaS_{1.5}Cl and the data for GaCl₄¹⁻ [16,17] are represented in Table 2. The exact agreement is obtained for both sets except for the discussed peak at 268 cm⁻¹. The formation of tetrahedral complex anion GaS_{1.5}Cl¹⁻ seems to be easier with tetrahedral glassy matrix GeS₂, so that at a ratio of Ga₂S₃ to TlCl equal to 1:2, the peak at 268 cm⁻¹ is invisible (Fig. 3), without GeS₂ one is distinguished yet (Fig. 5(a)) (maybe it is just a result of different resolution and content).

As said before, the increase of the metal ion radius at substitution of Tl by Cs in the glassy MGaS_{1.5}Cl results in radical changes of Raman spectra. Table 3 presents the experimental Raman frequencies of CsGaS_{1.5}Cl glass together with known data and the assignments for GaCl₃ melt [12,13] (these assignments are based on normal vibrations analysis of bridged X₂Y₆ molecules [14]; the observed bands are mostly assigned to the modes of the Ga₂Cl₆ dimer

It is really striking that all Raman bands of CsGaS_{1.5}Cl glass except the 215–230 cm⁻¹ region, correspond precisely to the band of GaCl₃ melt, i.e., to the vibration frequencies of dimer Ga₂Cl₆. Most dimer modes are assigned to the

Table 2 Raman frequencies (cm⁻¹)

GaCl ₄ ⁻¹ melt [16]	CsGaCl ₄ melt [17]	TlGaS _{1.5} Cl glass (this work)	CsGaS _{1.5} Cl melt, $T = 650^{\circ}$ C (this work)
115	120	~ 107	122
153	153	~ 174	172
		~ 271	
346	343	~ 316	315
380	370	~ 384	381

ring, that is, to the edge sharing tetrahedra. Hence we assume (taking into account similarity of S and Cl atoms weights) that in the Ga₂S₃-CsCl glass tetrahedral GaS_{3/2}Cl subunits are linked into chains by sharing common edges (Fig. 8(c)). Assumption about chain like structure in the system Ga₂S₃-Na₂S was proposed [15]. As the temperature is increased to 650°C (TL = 550°C), the Raman spectrum of CsGaS_{1.5}Cl changes, especially between 270°C and 400°C (see Fig. 6). We propose that in accordance with the proposed chain model the chains are destroyed and at about 500°C the spectrum is similar to the case of Tl-containing glass for which we propose the structure formed by the corner connected tetrahedra. However, in contrast to the glasses containing TlCl, the band at 268 cm⁻¹ appears to be absent (unless it is drowned by very broad main peak at $\sim 320 \text{ cm}^{-1}$). This absence points to the possibility that each Ga atom is saturated by fourfold coordina-

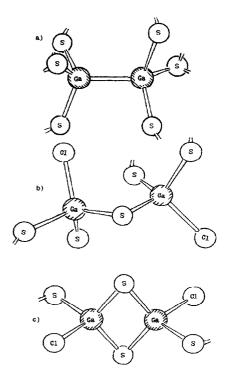


Fig. 8. Models of structure units proposed for Ga₂S₃-MCl (M - metal) glasses.

tion of S plus Cl. As can be seen from the Raman data for $GaCl_4^{1-}$ [16,17] in Table 2, there appear the same vibration energies as in the high temperature spectrum of $CsGaS_{1.5}Cl$.

Table 3
Raman frequencies (cm⁻¹)

CsGaS _{1.5} Cl (glass), this work	Ga ₂ Cl ₆ (melt), data and assignment [12]		Ga ₂ Cl ₆ (melt), data and assignment [13]	
86	96 vs	ν ₁₂ rocking	100 s	ν ₄ deformation
106	107 sh	ν ₇ wagging	113sh	v_{12} rocking
31			128 sh	v ₇ wagging
165	167 s	v_4 deformation	167 m	ν ₃ ring in-plane bend
	228 w	v_{15} symmetric twisting	215 sh	ν ₁₅ symmetric twisting
			231 w	v ₆ ring in-plane stretching
253	268 w	$v_9 * 2 = 246$ rocking	268 w	$\nu_3 + \nu_4$
317	321 m	v_3 ring in-plane bend	318 mw	v_2 ring breathing
343	342 ms	v_2 ring breathing	344 m	$(\nu_3 + \nu_4) * 2$
400	412 vs	v_1 symmetric stretching	413 s	ν ₁ symmetric stretching
	464 m	v ₁₁ antisymmetric stretching	462 m	ν ₁₁ antisymmetric stretching

5. Conclusion

Gallium in the chalcogenide/halogenide glasses is fourfold coordinated as in oxide glasses. At insufficient chalcogen/halogen content for tetrahedral environment of Ga, the fourth neighbour of gallium is gallium too (structure unit is shown in Fig. 8(a)). The addition of metal chloride to gallium sesquisulfide results in the formation of complex anion GaS_{3/2}Cl¹⁻. Stability of this complex depends on the cation size and increases along with increasing of the cation radius. The Ag+ cation has the smallest radius of the above mentioned cations - such a complex is not typical for Ag as for an outside cation. One is stable for Tl, but gallium-gallium coordination exists; for Cs with the largest radius among the discussed cations, the complex is stable up to 650°C and Ga is fully tetrahedral coordinated by chalcogen/halogen. The structure of TlGaS_{1.5}Cl glass and CsGaS_{1.5}Cl high temperature liquid is determined by corner connected tetrahedra (Fig. 8(b)), but the structure of CsGaS_{1.5}Cl glass is defined by tetrahedra connected by common edges into chains (Fig. 8(c)). The structure of Rb-containing glasses is determined by corner connected tetrahedra as well as by edge connected. Glass-forming ability follows the same sequence as complex stability.

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